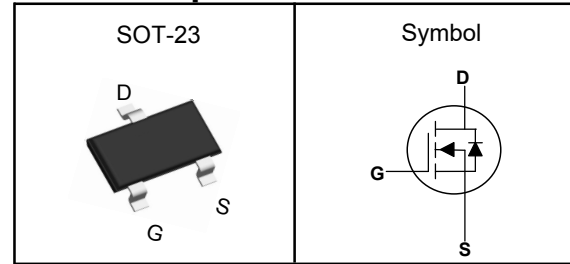


N-Channel Enhancement Mode MOSFET

Features

- Low $R_{ds(on)}$ for low conduction loss
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

Pin Description



Applications

- Power Management in Desktop Computer
- DC/DC Converters

V_{DSS}	110	V
$R_{DS(ON)-Typ}$	210	m Ω
I_D	3	A

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	110	V
V_{GSS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$I_{DM}^{①}$	Pulse Drain Current Tested	10	A
I_D	Continuous Drain Current	3	A
P_D	Maximum Power Dissipation	1.25	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C .

Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.



N-Channel Enhancement Mode MOSFET

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	110	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=110V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	---	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=1A$	---	210	240	m Ω
Dynamic Characteristics^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=50V, \text{Freq.}=1\text{MHz}$	---	190	---	pF
C_{oss}	Output Capacitance		---	22	---	
C_{rss}	Reverse Transfer Capacitance		---	13	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=1\Omega, I_D=1.3A, R_L=39\Omega$	---	6	---	nS
T_r	Turn-on Rise Time		---	10	---	
$T_{d(off)}$	Turn-off Delay Time		---	10	---	
T_f	Turn-off Fall Time		---	6	---	
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=1A$	1	---	---	S
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V, I_D=1.3A$	---	5.2	---	nC
Q_{gs}	Gate-Source Charge		---	0.75	---	
Q_{gd}	Gate-Drain Charge		---	1.4	---	
Source-Drain Characteristics ($T_J=25^{\circ}\text{C}$)						
$V_{SD}^{④}$	Diode Forward Voltage	$I_S=1A, V_{GS}=0V$	---	---	1.2	V

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

N-Channel Enhancement Mode MOSFET

Typical Characteristics

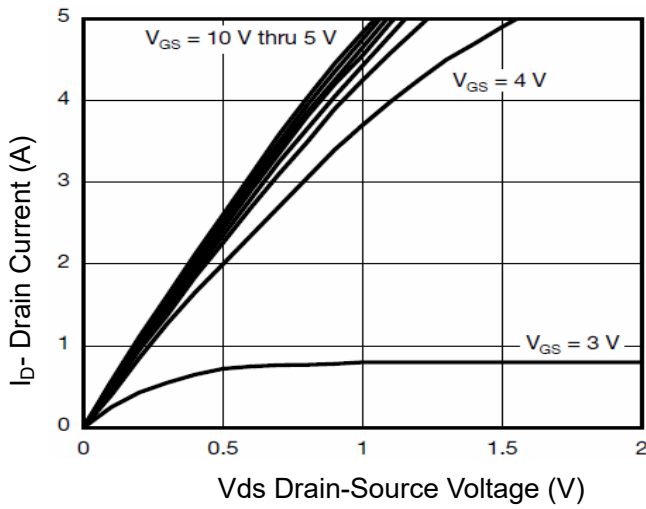


Figure 1 Output Characteristics

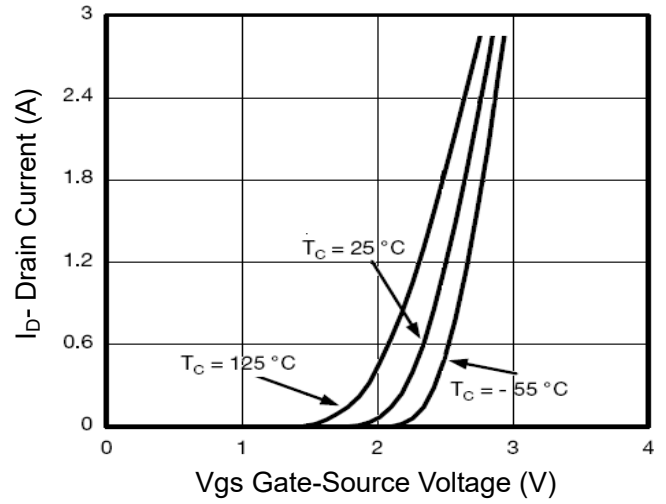


Figure 2 Transfer Characteristics

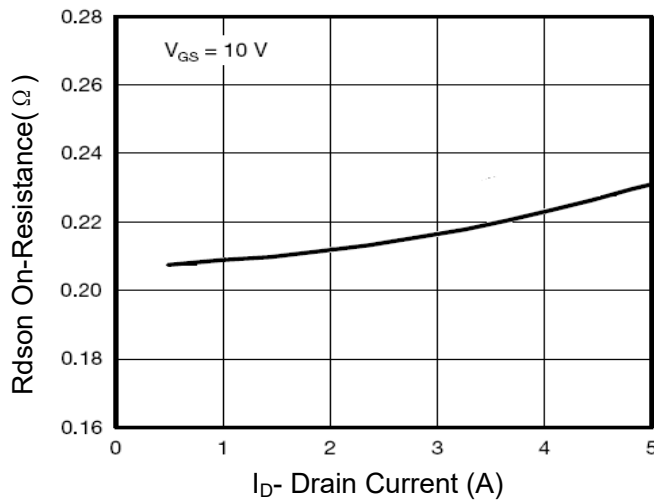


Figure 3 Rdson- Drain Current

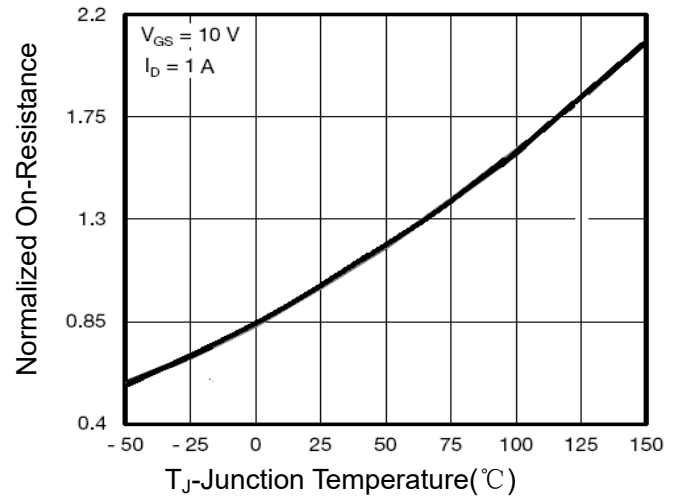


Figure 4 Rdson-Junction Temperature

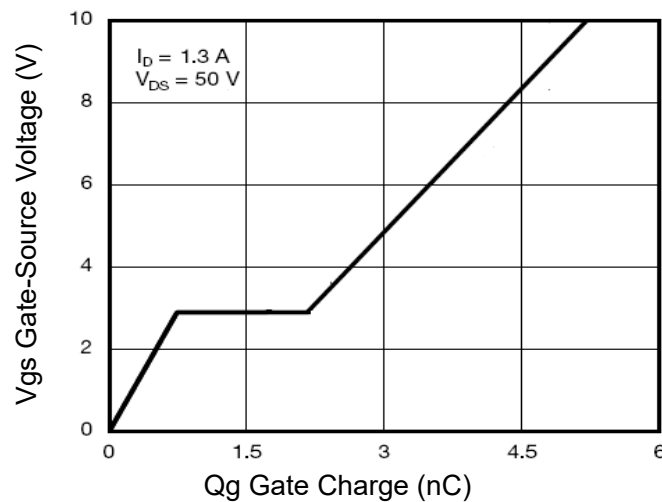


Figure 5 Gate Charge

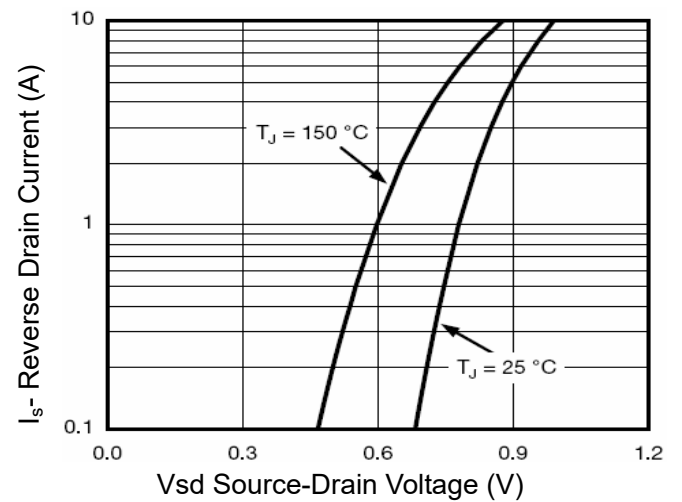


Figure 6 Source- Drain Diode Forward

N-Channel Enhancement Mode MOSFET

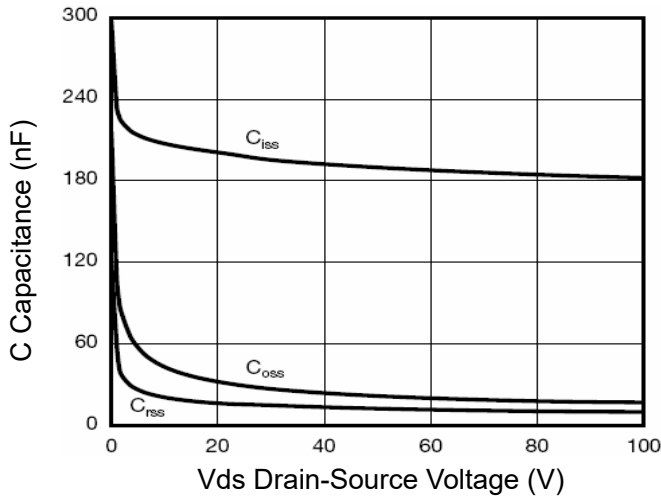


Figure 7 Capacitance vs Vds

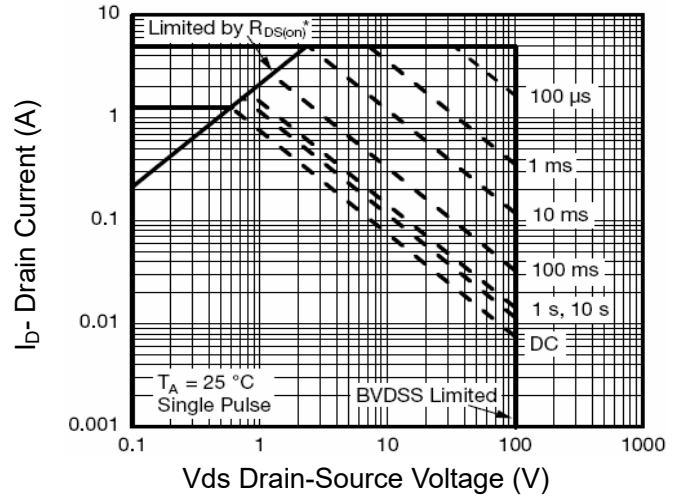


Figure 8 Safe Operation Area

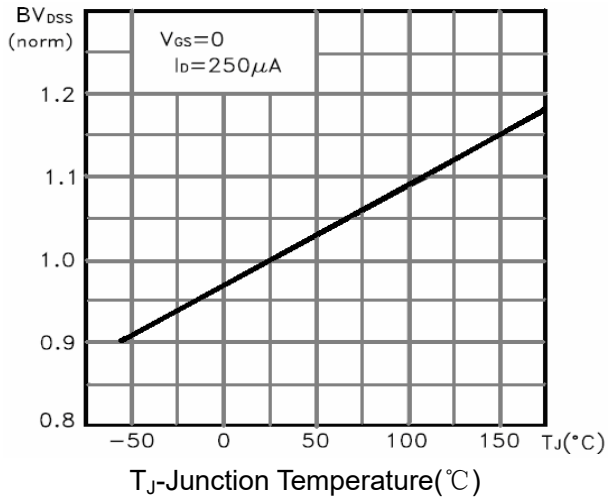


Figure 9 BV_{DSS} vs Junction Temperature

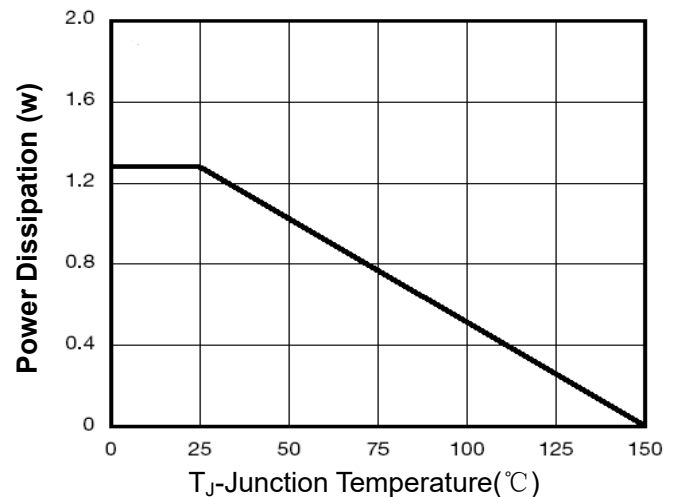


Figure 10 Power De-ratin

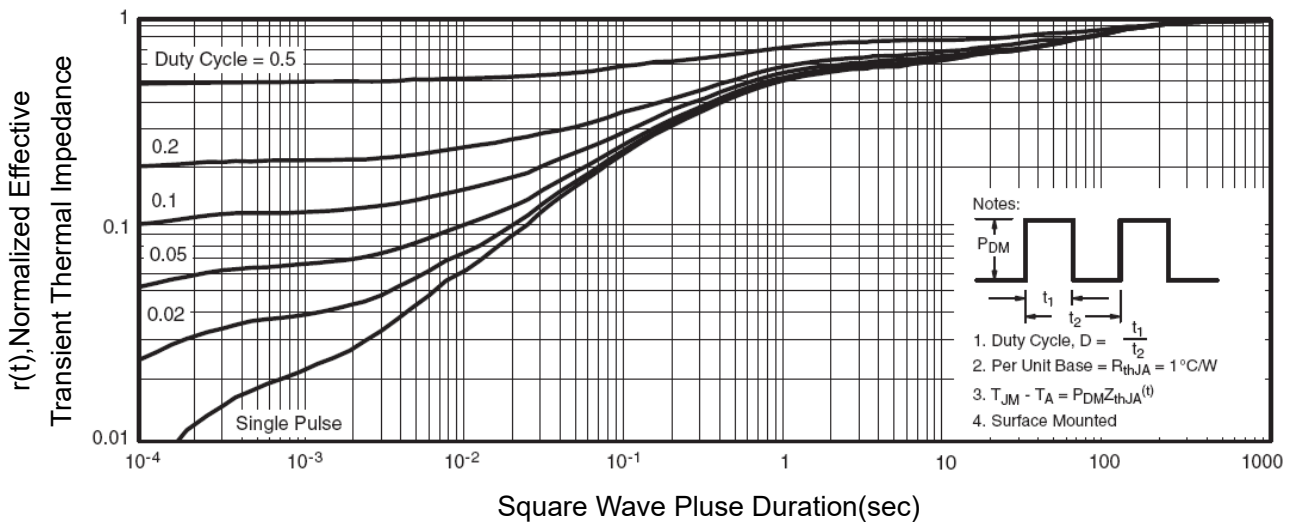
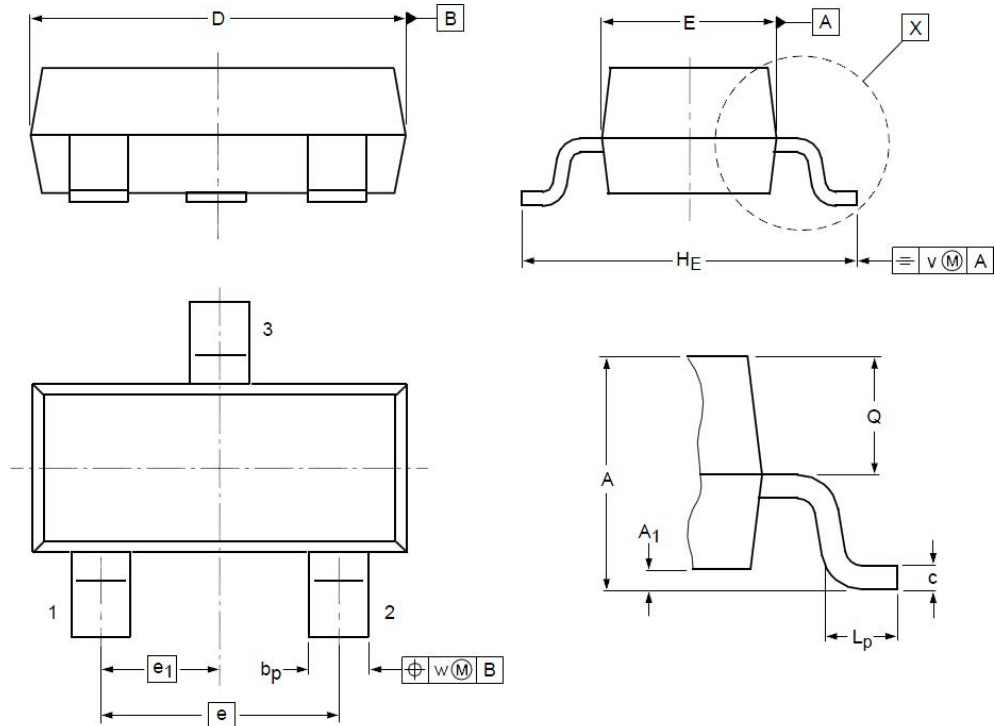


Figure 11 Normalized Maximum Transient Thermal Impedance

N-Channel Enhancement Mode MOSFET
SOT23 Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.05	1.20	e₁	--	0.95	--
A₁	0.01	0.05	0.10	H_E	2.10	2.40	2.50
b_p	0.38	0.42	0.48	L_p	0.40	0.50	0.60
c	0.09	0.13	0.15	Q	0.45	0.49	0.55
D	2.80	2.92	3.00	V	--	0.20	--
E	1.20	1.33	1.40	W	--	0.10	--
e	--	1.90	--				